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Team Nexperia

74HC4851-Q100; 74HCT4851-Q100

8-channel analog multiplexer/demultiplexer with injection-current effect control

Rev. 1 — 2 August 2012

Product data sheet

1. General description

The 74HC4851-Q100; 74HCT4851-Q100 are high-speed Si-gate CMOS devices and are specified in compliance with JEDEC standard no. 7A.

The 74HC4851-Q100; 74HCT4851-Q100 are 8-channel analog multiplexers/demultiplexers with three digital select inputs (S0 to S2), an active-LOW enable input (\overline{E}), eight independent inputs/outputs (Y0 to Y7) and a common input/output (Z). The devices feature injection-current effect control, which has excellent value in automotive applications where voltages in excess of the supply voltage are common.

With $\overline{\underline{E}}$ LOW, one of the eight switches is selected (low impedance ON-state) by S0 to S2. With $\overline{\underline{E}}$ HIGH, all switches are in the high-impedance OFF-state, independent of S0 to S2.

The injection-current effect control allows signals at disabled analog input channels to exceed the supply voltage without affecting the signal of the enabled analog channel. This eliminates the need for external diode/resistor networks typically used to keep the analog channel signals within the supply-voltage range.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Injection-current cross coupling < 1 mV/mA</p>
- Wide supply voltage range from 2.0 V to 6.0 V for 74HC4851-Q100
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Latch-up performance exceeds 100 mA per JESD 78 Class II level A
- Low ON-state resistance:
 - 400 Ω (typical) at $V_{CC} = 2.0 \text{ V}$
 - 215 Ω (typical) at $V_{CC} = 3.0 \text{ V}$
 - 120 Ω (typical) at $V_{CC} = 3.3 \text{ V}$
 - 76 Ω (typical) at $V_{CC} = 4.5 \text{ V}$
 - 59 Ω (typical) at $V_{CC} = 6.0 \text{ V}$



3. Applications

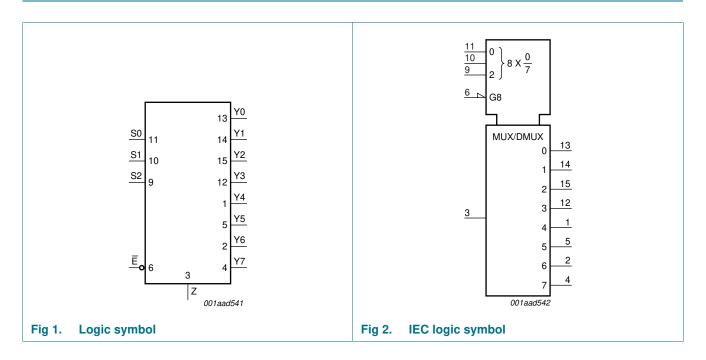
- Analog multiplexing and demultiplexing
- Digital multiplexing and demultiplexing
- Signal gating
- Automotive application

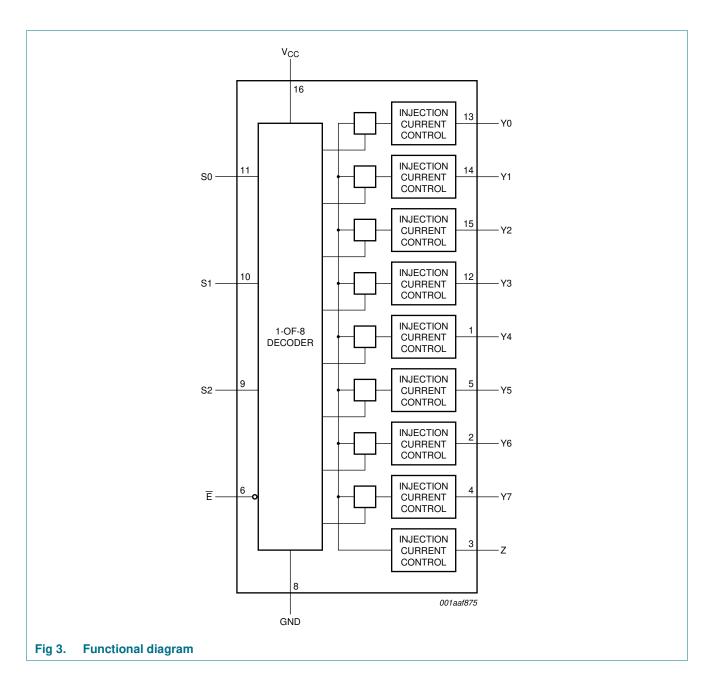
4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC4851D-Q100	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads;	SOT109-1
74HCT4851D-Q100			body width 3.9 mm	
74HC4851PW-Q100	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads;	SOT403-1
74HCT4851PW-Q100			body width 4.4 mm	
74HC4851BQ-Q100	–40 °C to +125 °C	DHVQFN16	F	SOT763-1
74HCT4851BQ-Q100			very thin quad flat package; no leads; 16 terminals; body $2.5 \times 3.5 \times 0.85$ mm	

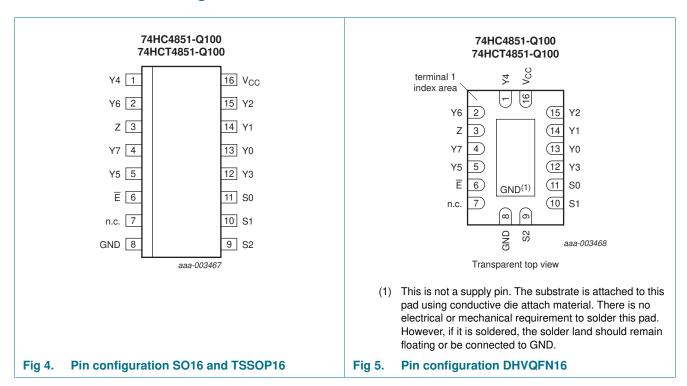
5. Functional diagram





6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
Y4	1	independent input/output
Y6	2	independent input/output
Z	3	common input/output
Y7	4	independent input/output
Y5	5	independent input/output
Ē	6	enable input (active LOW)
n.c.	7	not connected
GND	8	ground (0 V)
S2	9	select input
S1	10	select input
S0	11	select input
Y3	12	independent input/output
Y0	13	independent input/output
Y1	14	independent input/output
Y2	15	independent input/output
V _{CC}	16	supply voltage

74HC_HCT4851_Q100

7. Functional description

Table 3. Function table[1]

Input				Channel ON	
Ē	S2	S1	S0		
L	L	L	L	Y0 to Z	
L	L	L	Н	Y1 to Z	
L	L	Н	L	Y2 to Z	
L	L	Н	Н	Y3 to Z	
L	Н	L	L	Y4 to Z	
L	Н	L	Н	Y5 to Z	
L	Н	Н	L	Y6 to Z	
L	Н	Н	Н	Y7 to Z	
Н	X	Χ	X	-	

^[1] H = HIGH voltage level;

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		<i>y</i> , , , , , , , , , , , , , , , , , , ,		10	,
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		<u>[1]</u> –0.5	$V_{CC} + 0.5$	V
V_{SW}	switch voltage		<u>[2]</u> -0.5	$V_{CC} + 0.5$	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _{SK}	switch clamping current	V_{SW} < -0.5 V or V_{SW} > V_{CC} + 0.5 V	-	±20	mA
I _{SW}	switch current	$V_{SW} > -0.5 \text{ V or } V_{SW} < V_{CC} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[3]</u> _	500	mW

^[1] The minimum and maximum input voltage rating may be exceeded if the input clamping current rating is observed.

L = LOW voltage level;

X = don't care.

^[2] The minimum and maximum switch voltage rating may be exceeded if the switch clamping current rating is observed.

^[3] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
For TSSOP16 package: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
For DHVQFN16 packages: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	74H	C4851-	Q100	74H	ICT4851-	Q100	Unit
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	-	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_{SW}	switch voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
Δt/ΔV	input transition rise and	$V_{CC} = 2.0 \text{ V}$	-	6.0	1000	-	-	-	ns/V
	fall rate	$V_{CC} = 3.0 \text{ V}$	-	6.0	800	-	-	-	ns/V
		$V_{CC} = 3.3 \text{ V}$	-	6.0	800	-	-	-	ns/V
		$V_{CC} = 4.5 \text{ V}$	-	6.0	500	-	6.0	500	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	6.0	400	-	-	-	ns/V

10. Static characteristics

Table 6. R_{ON} (ON resistance)

At recommended operating conditions; voltages are referenced to GND (ground 0 V); For test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		-40 °C to	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC485	1-Q100		•	•						
R _{ON(peak)}	ON resistance	$V_I = V_{CC}$ to GND; $\overline{E} = V_{IL}$								
	(peak)	$V_{CC} = 2.0 \text{ V}; I_{SW} = 2 \text{ mA}$	-	400	650	-	670	-	700	Ω
		$V_{CC} = 3.0 \text{ V}; I_{SW} \leq 2 \text{ mA}$	-	215	330	-	360	-	380	Ω
		V_{CC} = 3.3 V; $I_{SW} \le 2 \text{ mA}$	-	120	270	-	305	-	345	Ω
		V_{CC} = 4.5 V; $I_{SW} \le 2 \text{ mA}$	-	76	210	-	240	-	270	Ω
		V_{CC} = 6.0 V; $I_{SW} \le 2 \text{ mA}$	-	59	195	-	220	-	250	Ω
ΔR_{ON}	ON resistance	$V_{I} = 0.5 \times V_{CC}; \overline{E} = V_{IL}$								
	mismatch between channels	$V_{CC} = 2.0 \text{ V}; I_{SW} = 2 \text{ mA}$	-	4	10	-	15	-	20	Ω
		V_{CC} = 3.0 V; $I_{SW} \le 2 \text{ mA}$	-	2	8	-	12	-	16	Ω
		$V_{CC} = 3.3 \text{ V}; I_{SW} \le 2 \text{ mA}$	-	2	8	-	12	-	16	Ω
		$V_{CC} = 4.5 \text{ V}; I_{SW} \le 2 \text{ mA}$	-	2	8	-	12	-	16	Ω
		$V_{CC} = 6.0 \text{ V}; I_{SW} \le 2 \text{ mA}$	-	3	9	-	13	-	18	Ω
74HCT48	51-Q100									
R _{ON(peak)}	ON resistance	$V_I = V_{CC}$ to GND; $\overline{E} = V_{IL}$								
	(peak)	$V_{CC} = 4.5 \text{ V}; I_{SW} \le 2 \text{ mA}$	-	76	210	-	240	-	270	Ω
ΔR_{ON}	ON resistance	$V_{I} = 0.5 \times V_{CC}; \overline{E} = V_{IL}$								
mismatch between channels		V_{CC} = 4.5 V; $I_{SW} \le 2 \text{ mA}$	-	2	8	-	12	-	16	Ω

Table 7. Injection current coupling

At recommended operating conditions; voltages are referenced to GND (ground 0 V); For test circuit see Figure 9.

Symbol	Parameter	Conditions			2100	74H	CT4851/0	2100	Unit
			Min	Typ[1]	Max	Min	Typ[1]	Max	
$T_{amb} = -40$	0 °C to +125 °C		'	'	•	•	'		
ΔV_{O}	output voltage	$ I_{SW} \le 1 \text{ mA}; R_S \le 3.9 \text{ k}\Omega$	[3]						
	variation	V _{CC} = 3.3 V	-	0.05	1	-	-	-	mV
		V _{CC} = 5.0 V	-	0.03	1	-	0.03	1	mV
		$ I_{SW} \leq 10 \text{ mA}; R_S \leq 3.9 \text{ k}\Omega$							
		$V_{CC} = 3.3 \text{ V}$	-	0.55	5	-	-	-	mV
		V _{CC} = 5.0 V	-	0.27	5	-	0.27	5	mV
		$ I_{SW} \le 1 \text{ mA}; R_S \le 20 \text{ k}\Omega$							
		$V_{CC} = 3.3 \text{ V}$	-	0.04	2	-	-	-	mV
		V _{CC} = 5.0 V	-	0.03	2	-	0.03	2	mV
		$ I_{SW} \le 10 \text{ mA}; R_S \le 20 \text{ k}\Omega$							
		$V_{CC} = 3.3 \text{ V}$	-	0.56	20	-	-	-	mV
		V _{CC} = 5.0 V	-	0.48	20	-	0.48	20	mV

^[1] Typical values are measured at $T_{amb} = 25$ °C.

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V);

				25 °C		-40 °C to +85 °C -40 °C to +125 °C			+125 °C	_
Symbol	Parameter	Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
74HC48	51-Q100		'	'			'	'		
V_{IH}	HIGH-level	control inputs								
	input voltage	$V_{CC} = 2.0 \text{ V}$	1.5	-	-	1.5	-	1.5	-	V
	vollage	$V_{CC} = 3.0 \text{ V}$	2.1	-	-	2.1	-	2.1	-	V
		$V_{CC} = 3.3 \text{ V}$	2.3	-	-	2.3	-	2.3	-	V
		$V_{CC} = 4.5 \text{ V}$	3.15	-	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	-	-	4.2	-	4.2	-	V
V _{IL} I	LOW-level	control inputs								
	input voltage	$V_{CC} = 2.0 \text{ V}$	-	-	0.5	-	0.5	-	0.5	V
	vollage	$V_{CC} = 3.0 \text{ V}$	-	-	0.9	-	0.9	-	0.9	V
		$V_{CC} = 3.3 \text{ V}$	-	-	1.0	-	1.0	-	1.0	V
		$V_{CC} = 4.5 \text{ V}$	-	-	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	-	1.8	-	1.8	-	1.8	V
II	input leakage	control inputs; V _I = GND or V _{CC}								
	current	$V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±0.1	-	±1.0	μΑ

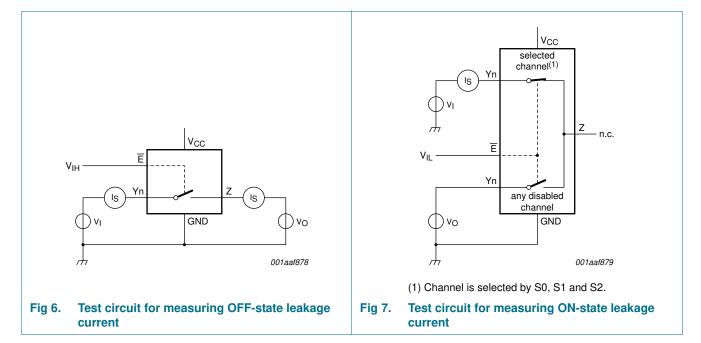
^[2] ΔV_0 here is the maximum variation of output voltage of an enabled analog channel when current is injected into any disabled channel.

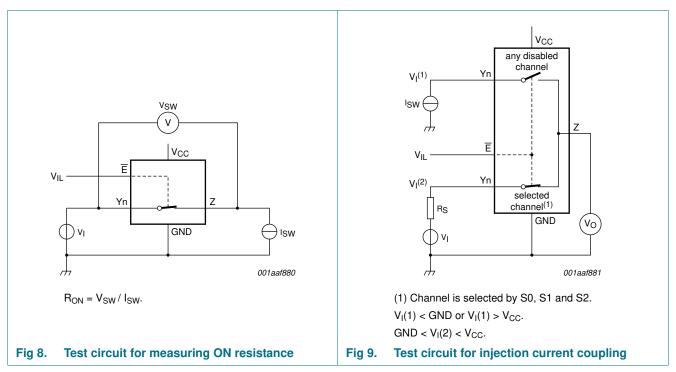
^[3] I_{SW} = total current injected into all disabled channels.

 Table 8.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground 0 V);

				25 °C		-40 °C t	to +85 °C	-40 °C to	+125 °C	;
Symbol	Parameter	Conditions	Min	Тур	Max	Min	Max	Min	Max	Uni
S(OFF)	OFF-state leakage current	$\overline{E} = V_{IH}; V_I = GND \text{ or } V_{CC};$ $V_O = V_{CC} \text{ or } GND;$ $V_{CC} = 6.0 \text{ V}; \text{ see } \underline{Figure 6}$								
		per channel	-	-	±0.1	-	±0.5	-	±1.0	μΑ
		all channels	-	-	±0.2	-	±2.0	-	±4.0	μΑ
I _{S(ON)}	ON-state leakage current	\overline{E} = V _{IL} ; V _I = GND or V _{CC} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V; see <u>Figure 7</u>	-	-	±0.1	-	±0.5	-	±1.0	μА
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; V_{CC} = 6.0 \text{ V}$	-	-	2.0	-	5.0	-	20.0	μΑ
Cı	input capacitance	S0, S1, S2 and \overline{E}	-	2	10	-	10	-	10	pF
C _{sw}	switch	Z; OFF-state	-	15	40	-	40	-	40	pF
	capacitance	Yn; OFF-state	-	3	15	-	15	-	15	рF
74HCT48	351-Q100									
V _{IH}	HIGH-level	control inputs								
	input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level	control inputs								
input voltage		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	8.0	-	0.8	-	0.8	V
l _l	input leakage	control inputs; $V_I = GND$ or V_{CC}								
	current	V _{CC} = 5.5 V	-	-	±0.1	-	±0.1	-	±1.0	μΑ
I _{S(OFF)}	OFF-state leakage current	\overline{E} = V _{IH} ; V _I = GND or V _{CC} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V; see <u>Figure 6</u>								
		per channel	-	-	±0.1	-	±0.5	-	±1.0	μΑ
		all channels	-	-	±0.2	-	±2.0	-	±4.0	μΑ
I _{S(ON)}	ON-state leakage current	\overline{E} = V _{IL} ; V _I = GND or V _{CC} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V; see <u>Figure 7</u>	-	-	±0.1	-	±0.5	-	±1.0	μА
I _{CC}	supply	$V_I = GND \text{ or } V_{CC}$								
	current	V _{CC} = 5.5 V	-	-	2.0	-	5.0	-	20.0	μΑ
Δl _{CC}	additional supply current	control inputs; $V_{I} = V_{CC} - 2.1 \text{ V};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}; I_{O} = 0 \text{ A}$	-	-	300	-	370	-	370	μА
Cı	input capacitance	S0, S1, S2 and \overline{E}	-	2	10	-	10	-	10	pF
C _{sw}	switch	Z; OFF-state	-	15	40	-	40	-	40	рF
	capacitance	Yn; OFF-state	-	3	15	-	15	-	15	рF





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11. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for load circuit see Figure 14.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
74HC485	51-Q100										
t _{pd}	propagation delay	Z, Yn to Yn, Z; see Figure 10	[1]								
		$V_{CC} = 2.0 \text{ V}$		-	10.0	25	-	29	-	32	ns
		V _{CC} = 3.0 V		-	6.0	15.5	-	17.5	-	19.5	ns
		$V_{CC} = 3.3 \text{ V}$		-	5.0	14.5	-	16.5	-	18.5	ns
		$V_{CC} = 4.5 \text{ V}$		-	4.0	11.5	-	12.5	-	13.5	ns
		$V_{CC} = 6.0 \text{ V}$		-	3.0	10	-	11	-	12	ns
		Sn to Z, Yn; see <u>Figure 11</u>	[1]								
		V _{CC} = 2.0 V		-	18.0	32	-	35	-	40	ns
		$V_{CC} = 3.0 \text{ V}$		-	9.5	17.5	-	20	-	23	ns
		V _{CC} = 3.3 V		-	8.5	16.5	-	19	-	22	ns
		$V_{CC} = 4.5 \text{ V}$		-	6.5	13	-	15	-	17	ns
		$V_{CC} = 6.0 \text{ V}$		-	5.0	12.5	-	14.5	-	16.5	ns
t _{en}	enable time	E to Z, Yn; see Figure 12	[2]								
		$V_{CC} = 2.0 \text{ V}$		-	-	95	-	105	-	115	ns
		$V_{CC} = 3.0 \text{ V}$		-	-	90	-	100	-	110	ns
		$V_{CC} = 3.3 \text{ V}$		-	-	85	-	95	-	105	ns
		V _{CC} = 4.5 V		-	-	80	-	90	-	100	ns
		$V_{CC} = 6.0 \text{ V}$		-	-	78	-	80	-	80	ns
t _{dis}	disable time	E to Z, Yn; see Figure 12	[3]								
		$V_{CC} = 2.0 \text{ V}$		-	-	99	-	105	-	115	ns
		$V_{CC} = 3.0 \text{ V}$		-	-	90	-	100	-	110	ns
		$V_{CC} = 3.3 \text{ V}$		-	-	85	-	95	-	105	ns
		V _{CC} = 4.5 V		-	-	80	-	90	-	100	ns
		$V_{CC} = 6.0 \text{ V}$		-	-	78	-	80	-	80	ns
C_{PD}	power dissipation capacitance	per channel; see <u>Figure 12</u>	[4]								
		$V_{CC} = 3.3 \text{ V}$		-	28	-	-	-	-	-	pF
		$V_{CC} = 5.0 \text{ V}$		-	33	-	-	-	-	-	pF

 Table 9.
 Dynamic characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for load circuit see Figure 14.

	05.00			_							
Symbol	Parameter	Conditions			25 °C		–40 °C	to +85 °C	–40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
74HCT48	351-Q100										
t _{pd}	propagation delay	Z, Yn to Yn, Z; see Figure 10	[1]								
		$V_{CC} = 4.5 \text{ V}$		1.6	3.7	11.5	1.1	12.5	1.1	13.5	ns
		Sn to Z, Yn; see <u>Figure 11</u>	<u>[1]</u>								
		$V_{CC} = 4.5 \text{ V}$		3.2	8.0	13	2.3	15	2.3	17	ns
t _{en}	enable time	E to Z, Yn; see Figure 12	[2]								
		$V_{CC} = 4.5 \text{ V}$		4.2	8.6	25	3.0	30	3.0	35	ns
t _{dis}	disable time	E to Z, Yn; see Figure 12	[3]								
		$V_{CC} = 4.5 \text{ V}$		28.5	64.7	80	28.2	90	28	100	ns
C_{PD}	power dissipation capacitance	per channel; see <u>Figure 13</u>	[4]								
		$V_{CC} = 5.0 \text{ V}$		-	30	-	-	-	-	-	pF

- [1] tpd is the same as tplH and tpHL.
- [2] t_{en} is the same as t_{PZH} and t_{PZL} .
- [3] t_{dis} is the same as t_{PLZ} and t_{PHZ} .
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum \{(C_L + C_{sw}) \times V_{CC}^2 \times f_o\} \text{ where: }$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

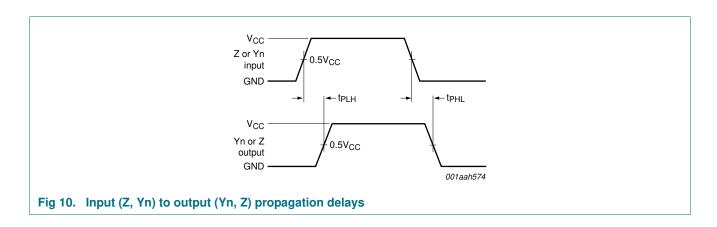
 $\sum \{(C_L + C_{sw}) \times V_{CC}^2 \times f_0\} = \text{sum of outputs};$

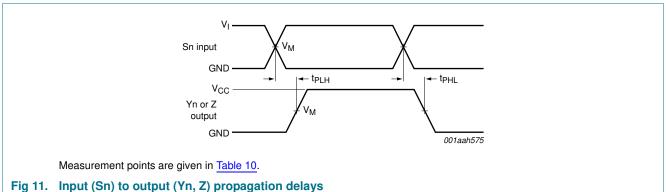
C_L = output load capacitance in pF;

C_{sw} = switch capacitance in pF;

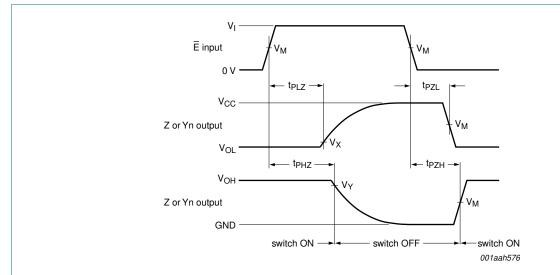
 V_{CC} = supply voltage in V.

12. Waveforms





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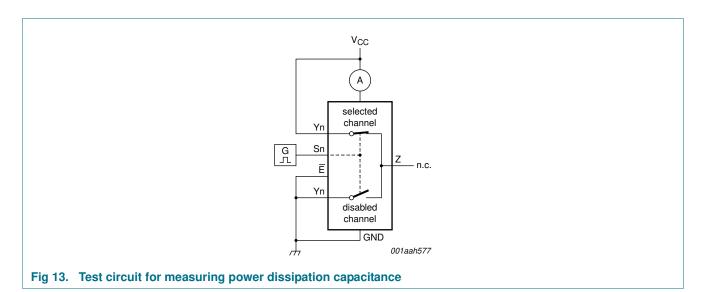
Measurement points are given in Table 10.

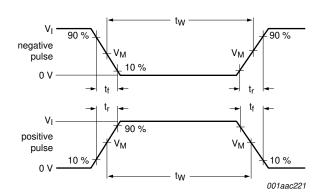
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 12. Enable and disable times

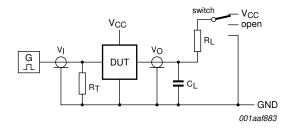
Table 10. Measurement points

Туре	Input		Output		
	V _M	VI	V _M	V _X	V _Y
74HC4851-Q100	0.5V _{CC}	V _{CC}	0.5V _{CC}	$V_{OL} + 0.1(V_{CC} - V_{OL})$	0.9V _{OH}
74HCT4851-Q100	1.3 V	3.0 V	0.5V _{CC}	$V_{OL} + 0.1(V_{CC} - V_{OL})$	0.9V _{OH}





a. Input pulse definition



Definitions for test circuit:

R_L = load resistance.

 C_L = load capacitance including jig and probe capacitance.

 R_T = termination resistance should be equal to the output impedance Z_0 of the pulse generator.

b. Load circuit

Test data is given in Table 11.

Fig 14. Input pulse definition and load circuit

Table 11. Test data

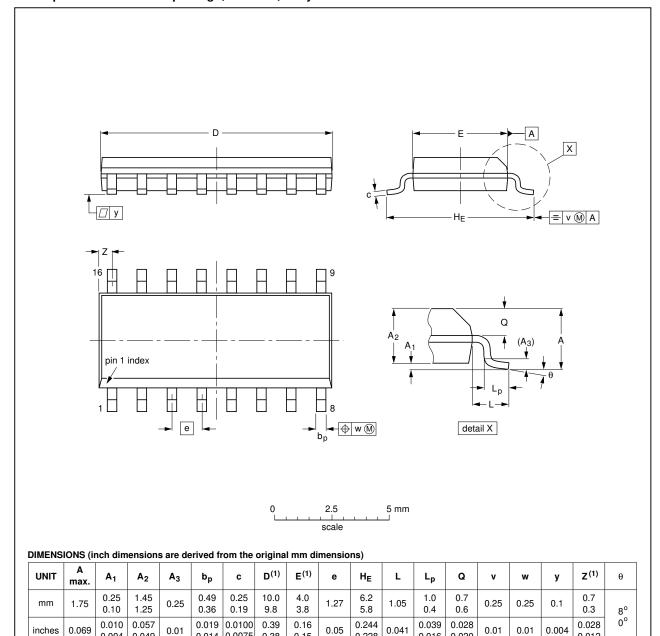
Test	Input			Output	S1 position			
	Control E, Sn	Switch Yn (Z)	t _r , t _f	Switch Z (Y	Switch Z (Yn)			
	V <u>[1]</u>	VI		CL	R _L			
t _{PHL} , t _{PLH}	V _{CC}	V _{CC}	6 ns	50 pF	-	open		
t _{PHZ} , t _{PZH}	V_{CC}	V_{CC}	6 ns	50 pF	10 kΩ	GND		
t _{PLZ} , t _{PZL}	V_{CC}	V _{CC}	6 ns	50 pF	10 kΩ	V_{CC}		
C _{PD}	V_{CC}	V _{CC}	6 ns	0 pF	-	open		

[1] For 74HCT4851-Q100: input voltage $V_1 = 3.0 \text{ V}$.

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

0.014 0.0075

0.38

0.15

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012				99-12-27 03-02-19	

0.228

0.016

Fig 15. Package outline SOT109-1 (SO16)

0.004

0.049

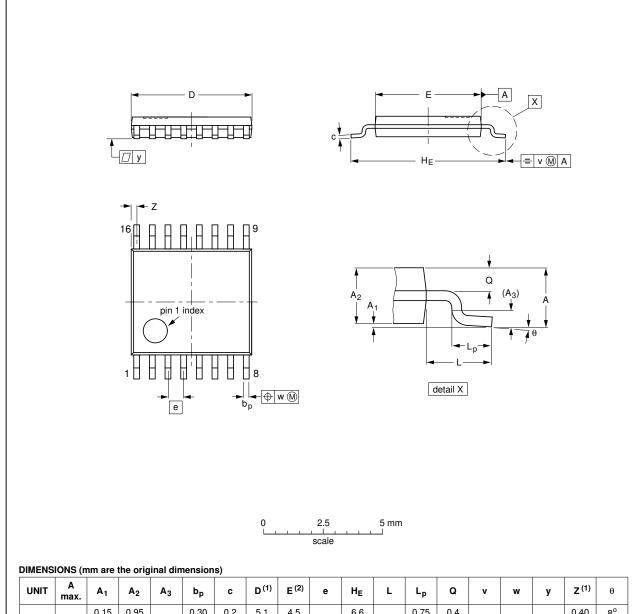
74HC HCT4851 Q100

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



						-,												
UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E (2)	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT403-1		MO-153				-99-12-27 03-02-18	
•		•					•

Fig 16. Package outline SOT403-1 (TSSOP16)

74HC_HCT4851_Q100

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DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

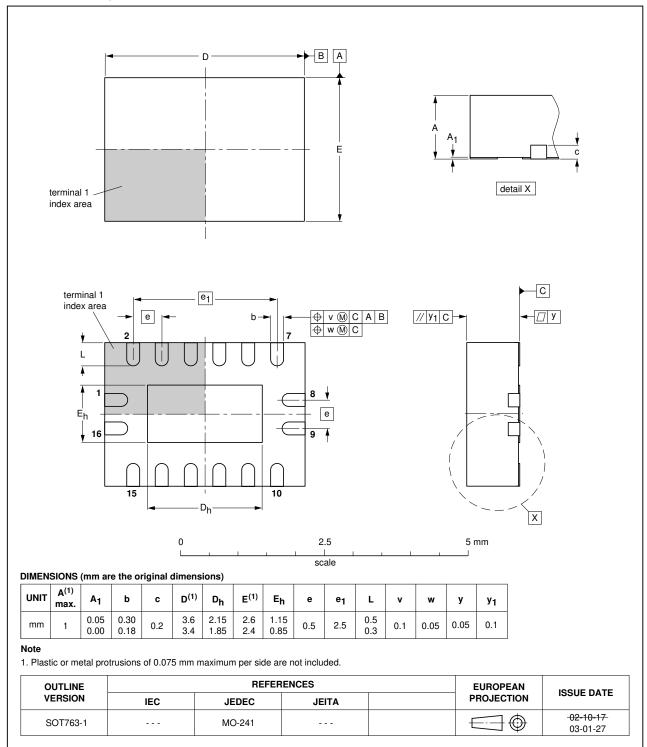


Fig 17. Package outline SOT763-1 (DHVQFN16)

74HC_HCT4851_Q100

14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
MIL	Military

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT4851_Q100 v.1	20120802	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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74HC4851-Q100; 74HCT4851-Q100

8-channel analog multiplexer/demultiplexer with injection-current effect control

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NXP Semiconductors

74HC4851-Q100; 74HCT4851-Q100

8-channel analog multiplexer/demultiplexer with injection-current effect control

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